

New Jersey Semi-Conductor Products, Inc.

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U.S.A.

JEDEC TYPE # 2N541, 2N542, 2N543

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TRANSITRON

1. General Description:

This transistor is a NPN silicon triode transistor designed primarily for low level, IF and RF amplifier applications in the Audio & RF frequency range for industrial service.

11. Mechanical Data:

A. Outline Drawings

1. Outline is in accordance with TO-5 pkg.
2. Terminal Designation
 1. Emitter
 2. Base
 3. Collector

111. Absolute Maximum Ratings:

A. Maximum Temperature

1. Storage Temperature -65°C to 200°C
2. Lead Temperature, 1/16" ± 1/32" from case for 8 seconds 230°C

B. Maximum Reverse Rating

- | | | | |
|--------------------------------|-------|-------|-------|
| | 2N541 | 2N542 | 2N543 |
| 1. Emitter-base voltage @ 25°C | 2V | 2V | 2V |
| 2. Collector-base voltage | 15V | 30V | 45V |
| 3. Collector-emitter voltage | 15V | 30V | 45V |

C. Maximum Current (DC)

1. Collector Current, I_C 25 ma.

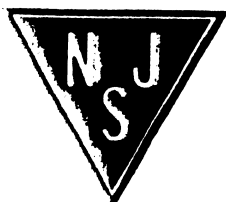
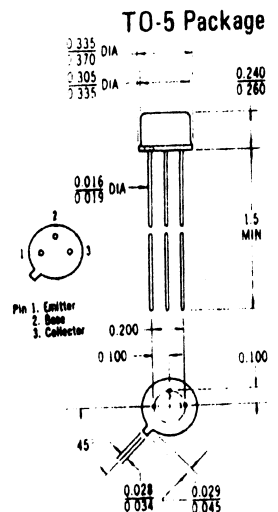
D.

1. Maximum Power Dissipation @ 25°C ambient 0.2 watts
2. Derating Factor .0012 watts/°C

IV. Electrical Characteristics, 25°C:

A. Static Characteristics

		Min.	Max.
1. Collector Current, I_{CBO}	I_{CBO}		0.5 μ a.
Collector Current, I_{CBO} @ 150°C	I_{CBO} @ 150°C		50 μ a.
Collector Voltage, V_{CB}	V_{CB} = Ratings of 111 -B2		
2. Emitter Current, I_{EBO}	I_{EBO}		0.5 μ a.
Emitter Voltage, V_{EB}	V_{EB} = 2V		
3. DC Saturation Voltage			1.5 V
Collector Current	5 ma		
Base Current	2.2 ma		



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